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Sut	stitute for form 1449A/B/PT	0		Complete if Known			
		•		Application Number	10/665,757	(Conf. No. 6828)	
11	IFORMATION	N DI	SCLOSURE	Filing Date	September 19	, 2003	
STATEMENT BY APPLICANT				First Named Inventor	Glenn J. Leedy		
_			-	Art Unit	2822		
(Use as many sheets as necessary)				Examiner Name	Pamela E. Perkins		
Sheet	1	of	3	Attorney Docket Number	ELM-1 Cont.9	,	

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Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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	saudio los lossis (4407401)	•		Application Number	10/665,757	(Conf. No. 6828)	
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l s	TATEMENT 8	3Y /	APPLICANT	First Named Inventor	Glenn J. Leedy		
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Sheet	2	of	3	Attorney Docket Number	ELM-1 Cont.9)	

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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"	,34,41,5 107 101111 1 7 7 5 7 2 11 1	_		Application Number	10/665,757	(Conf. No. 6828)	
11	NFORMATION	N DI	SCLOSURE	Filing Date	September 19, 2003 Glenn J. Leedy		
S	TATEMENT	BY /	APPLICANT	First Named Inventor			
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Suc	Sulue for form 1448/CD/F			Application Number	10/665,757	(Conf. No. 6828)	
11	NFORMATION	IQ N	SCLOSURE	Filing Date	September 19, 2003		
	TATEMENT			First Named Inventor	Glenn J. Leedy 2822		
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